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	1325	(EVANS SAME DAVID) OR (HSU SAME (SHENG OR TENG)) OR (ULRICH SAME BRUCE) OR (TWEET SAME DOUGLAS)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	72003/11/12 17:54
2	1325	(EVANS SAME DAVID) OR (HSU SAME (SHENG OR TENG)) OR (ULRICH SAME BRUCE) OR (TWEET SAME DOUGLAS) OR (STECKER SAME LISA)	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/11/12
3	98	((EVANS SAME DAVID) OR (HSU SAME (SHENG OR TENG)) OR (ULRICH SAME BRUCE) OR (TWEET SAME DOUGLAS) OR (STECKER SAME LISA)) AND CMOS	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/12
4	37	(((EVANS SAME DAVID) OR (HSU SAME (SHENG OR TENG)) OR (ULRICH SAME BRUCE) OR (TWEET SAME DOUGLAS) OR (STECKER SAME LISA)) AND CMOS) and (sti or (shallow adj trench adj isolation) or (trench same isolation))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/12
5	19	((((EVANS SAME DAVID) OR (HSU SAME (SHENG OR TENG)) OR (ULRICH SAME BRUCE) OR (TWEET SAME DOUGLAS) OR (STECKER SAME LISA)) AND CMOS) and (sti or (shallow adj trench adj isolation) or (trench same isolation))) and polysilicon and (cmp or (chemical adj mechanical\$2 adj planariz\$5))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/12
6	15	((((EVANS SAME DAVID) OR (HSU SAME (SHENG OR TENG)) OR (ULRICH SAME BRUCE) OR (TWEET SAME DOUGLAS) OR (STECKER SAME LISA)) AND CMOS) and (sti or (shallow adj trench adj isolation) or (trench same isolation))) and polysilicon and (cmp or (chemical adj mechanical\$2 adj planariz\$5))) and (thickness or thick) and (depth or deep)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/12 17:58
-	2961   	((438/207) or (438/218) or (438/219) or (438/221) or (438/401) or (438/404) or (438/424)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/12   16:27
-   	660   	(((438/207) or (438/218) or (438/219) or (438/221) or (438/401) or (438/404) or (438/424)).CCLS.) and (cmos or (complementary adj metal adj oxide adj semiconductor))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/12
	459   	(((((438/207) or (438/218) or (438/219) or (438/221) or (438/401) or (438/404) or (438/424)).CCLS.) and (cmos or (complementary adj metal adj oxide adj semiconductor))) and ((trench same isolation) or (shallow ajd trench adj isolation) or sti)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/12 16:31
-	432	((((438/207) or (438/218) or (438/219) or (438/221) or (438/401) or (438/404) or (438/424)).CCLS.) and (cmos or (complementary adj metal adj oxide adj semiconductor))) and polysilicon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/12 16:31
	309	(((((438/207) or (438/218) or (438/219) or (438/221) or (438/401) or (438/404) or (438/424)).CCLS.) and (cmos or (complementary adj metal adj oxide adj semiconductor))) and polysilicon) and ((trench same isolation) or (shallow ajd trench adj isolation) or sti)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/12

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		or (438/221) or (438/401) or (438/404) or	US-PGPUB;	16:33
		(438/424)).CCLS.) and (cmos or	EPO; JPO;	i i
		(complementary adj metal adj oxide adj	DERWENT;	!
i l		semiconductor))) and polysilicon) and	IBM_TDB	
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		trench adj isolation) or sti)) and		į l
		(thickness or thick) and (depth or deep)	 	ĺ
ı <b>-</b>	103	(((((((438/207) or (438/218) or (438/219)	USPAT;	2003/11/12
		or (438/221) or (438/401) or (438/404) or	US-PGPUB;	16:38
!		(438/424)).CCLS.) and (cmos or	EPO; JPO;	l i
!		(complementary adj metal adj oxide adj	DERWENT;	
1		semiconductor))) and polysilicon) and	IBM TDB	]
		((trench same isolation) or (shallow ajd	i -	i i
!		trench adj isolation) or sti)) and	1	)
i i		(thickness or thick) and (depth or deep))	I	!
		and (cmp or (chemical adj mechanical\$2		İ
i		adi planariz\$5))	:	
i -	9	((((((((438/207)  or  (438/218)  or	USPAT;	2003/11/12
	_	(438/219) or (438/221) or (438/401) or	US-PGPUB;	17:51
1		(438/404) or (438/424)).CCLS.) and (cmos	EPO; JPO;	1
i		or (complementary adj metal adj oxide adj	DERWENT;	}
		semiconductor))) and polysilicon) and	IBM TDB	ì
		((trench same isolation) or (shallow ajd		
į.		trench adj isolation) or sti)) and		1
		(thickness or thick) and (depth or deep))		1
i		and (cmp or (chemical adj mechanical\$2	i	<b>i</b>
·		adj planariz\$5))) and (alignment same		!
		(mark\$3 or key))	Į	İ
l l		(11022117 02 11311)	: <del></del>	⊥ l